

Remarks

1. Amendment of the specification:

5 The main feature of the present invention is forming a thin film transistor with two dielectric layers thereon. Some typos and improper descriptions are corrected in the amended specification. No new matter is introduced in the above-mentioned amendment.
10 Allowance for making the above-mentioned amendment is politely requested.

2. Amendment of claims 1 and 4:

15 Claim 4 is combined to claim 1 and therefore cancelled. No new matter is introduced in the above-mentioned amendment. Allowance for making the above-mentioned amendment is politely requested.

20 3. Amendment of claims 1, 2, 7, 8, 11, and 12:

25 Claims 1, 2, 7, 8, 11, and 12 are amended to be identical with the amended descriptions in the specification. No new matter is introduced in the above-mentioned amendment. Allowance for making the above-mentioned amendment is politely requested.

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Sincerely yours,

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